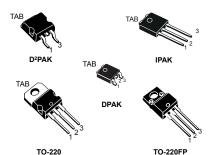
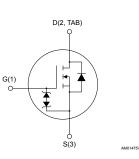


STB3NK60ZT4, STD3NK60Z-1, STD3NK60ZT4 STP3NK60Z, STP3NK60ZFP

Datasheet

N-channel 600 V, 3.2 Ω typ., 2.4 A SuperMESH[™] Power MOSFETs in D²PAK, IPAK, DPAK, TO-220 and TO-220FP packages





Features

Order codes	V _{DS}	R _{DS(on)} max.	۱ _D	Package
STB3NK60ZT4				D ² PAK
STD3NK60Z-1	600 V	3.6 Ω	2.4 A	IPAK
STD3NK60ZT4				DPAK
STP3NK60Z				TO-220
STP3NK60ZFP				TO-220FP

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitance
- Zener-protected

Applications

Switching applications

Description

These high-voltage devices are Zener-protected N-channel Power MOSFETs developed using the SuperMESH[™] technology by STMicroelectronics, an optimization of the well-established PowerMESH[™]. In addition to a significant reduction in on-resistance, these devices are designed to ensure a high level of dv/dt capability for the most demanding applications.

Product status link
STB3NK60ZT4
STD3NK60Z-1
STD3NK60ZT4
STP3NK60Z
STP3NK60ZFP



1 Electrical ratings

O week of	Deremeder		Value		11
Symbol	Parameter	D ² PAK, TO-220	TO-220FP	DPAK, IPAK	Unit
V _{DS}	Drain-source voltage		600		V
V _{GS}	Gate-source voltage	±30		V	
ID	Drain current (continuous) at T_C = 25 °C	2.4	2.4 (1)	2.4	А
ID	Drain current (continuous) at T_C = 100 °C	1.51	1.51 ⁽¹⁾	1.51	А
I _{DM} ⁽²⁾	Drain current (pulsed)	9.6	9.6 (1)	9.6	А
P _{TOT}	Total dissipation at T_C = 25 °C	45	20	45	W
ESD	Gate-source human body model (R = 1.5 k Ω , C = 100 pF)	2.1			kV
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat-sink (t = 1 s, T_C = 25 °C)		2.5		kV
dv/dt (3)	Peak diode recovery voltage slope	4.5			V/ns
Tj	Operating junction temperature range			°C	
T _{stg}	Storage temperature range	-55 to 150		-0	

Table 1. Absolute maximum ratings

1. Limited by maximum junction temperature.

2. Pulse width limited by safe operating area.

3. $I_{SD} \leq 2.4 \text{ A}, \text{ di/dt} \leq 200 \text{ A/}\mu\text{s}, V_{DSpeak} \leq V_{(BR)DSS}, V_{DD} = 80\% V_{(BR)DSS}.$

Table 2. Thermal data

Sumbol		Value					Unit
Symbol	Parameter	D ² PAK	TO-220	TO-220FP	DPAK	IPAK	Unit
R _{thj-case}	Thermal resistance junction-case		2.78	6.25	2.	78	°C/W
R _{thj-amb}	Thermal resistance junction- ambient		62	2.5		100	°C/W
R _{thj-pcb} ⁽¹⁾	Thermal resistance junction-pcb	35			50		°C/W

1. When mounted on an 1-inch² FR-4, 2oz Cu board.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I _{AR}	Avalanche current, repetitive or not- repetitive (pulse width limited by T _j Max)	2.4	А
E _{AS}	Single pulse avalanche energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	150	mJ



2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1 mA, V _{GS} = 0 V	600			V
1	Zero gate voltage drain	V_{GS} = 0 V, V_{DS} = 600 V			1	μA
IDSS	current	V_{GS} = 0 V, V_{DS} = 600 V, T_{C} = 125 °C $^{(1)}$			50	μA
I _{GSS}	Gate body leakage current	V _{DS} = 0 V, V _{GS} = ±20 V			±10	μA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 50 \ \mu A$	3	3.75	4.5	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10 V, I _D = 1.2 A		3.2	3.6	Ω

Table 4. On/off states

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance			311		
C _{oss}	Output capacitance	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0 V	_	43	-	pF
C _{rss}	Reverse transfer capacitance			8		
C _{oss eq.} ⁽¹⁾	Equivalent output capacitance	V_{DS} = 0 to 480 V, V_{GS} = 0 V	-	26	-	pF
Qg	Total gate charge	V _{DD} = 480 V, I _D = 2.4 A, V _{GS} = 0 to 10 V		11.8	-	
Q _{gs}	Gate-source charge	(see Figure 16. Test circuit for gate charge	-	2.6		nC
Q _{gd}	Gate-drain charge	behavior)		6.4	-	

1. $C_{oss eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 300 V, I _D = 1.5 A,		9		
tr	Rise time	R_G = 4.7 Ω , V_{GS} = 10 V		14		
t _{d(off)}	Turn-off delay time	(see Figure 15. Test circuit for resistive load switching times and Figure 20. Switching	-	19	-	ns
t _f	Fall time	time waveform)		14		

Table 7. Source drain diode

Symbol	Parameter Test conditions		Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current				2.4	
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)		-		9.6	A
V _{SD} ⁽²⁾	Forward on voltage	I_{SD} = 2.4 A, V_{GS} = 0 V	-		1.6	V
t _{rr}	Reverse recovery time	I _{SD} = 2.4 A, di/dt = 100 A/µs		306		ns
Q _{rr}	Reverse recovery charge	V_{DD} = 48 V, T _j = 150°C (see Figure 17. Test	-	948		nC
I _{RRM}	Reverse recovery current	circuit for inductive load switching and diode recovery times)		6.2		А

1. Pulse width limited by safe operating area.

2. Pulsed: pulse duration = 300 µs, duty cycle 1.5%.

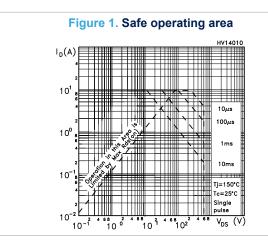
Table 8. Gate-source Zener diode

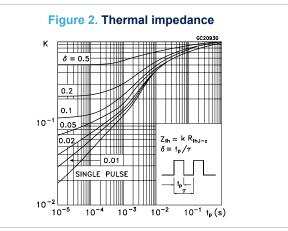
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)GSO}	Gate-source breakdown voltage	$I_{GS} = \pm 1 \text{ mA}, I_D = 0 \text{ A}$	±30	-	-	V

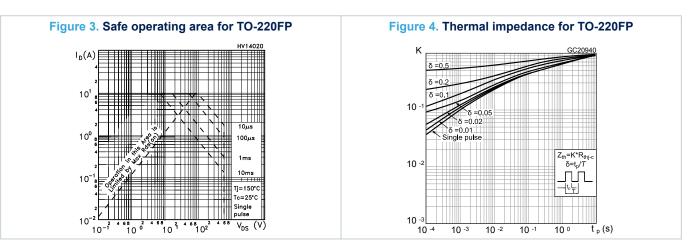
The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

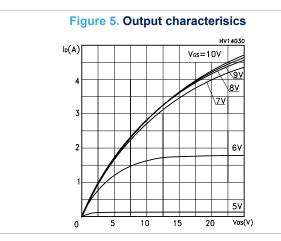


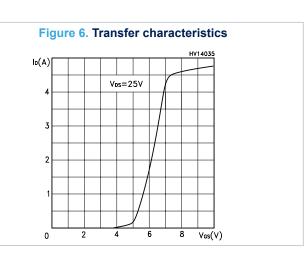
2.1 Electrical characteristics curves













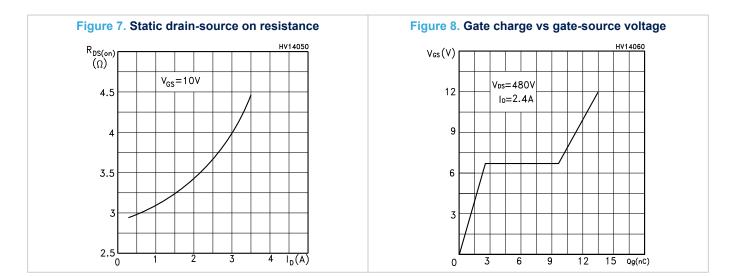


Figure 9. Capacitance variations HV14070 C(pF) f=1MHz 600 V_{gs}=0V 400 Ciss 200 Cos

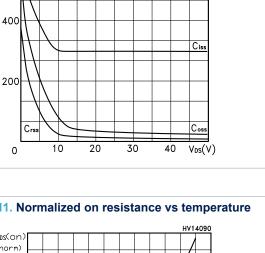
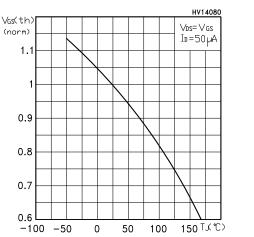


Figure 10. Normalized gate threshold voltage vs temperature



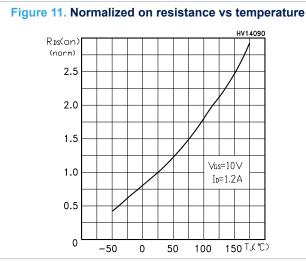
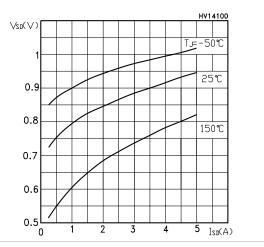
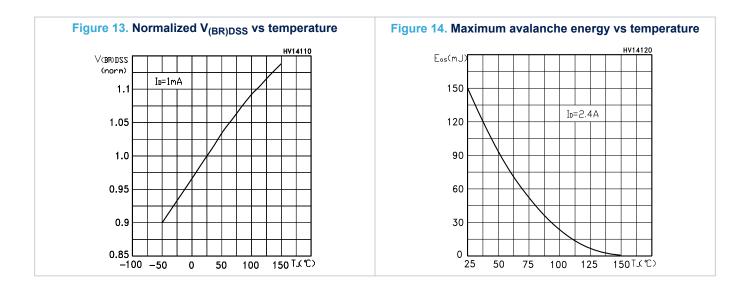


Figure 12. Source-drain diode forward characteristic

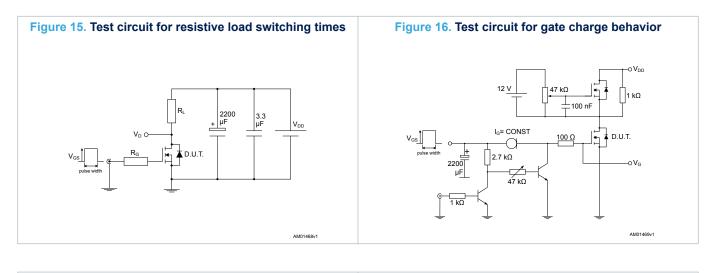


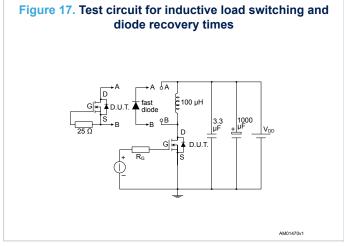


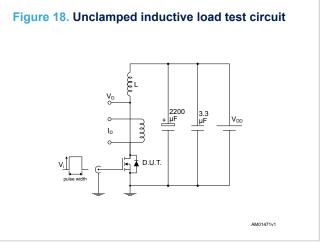


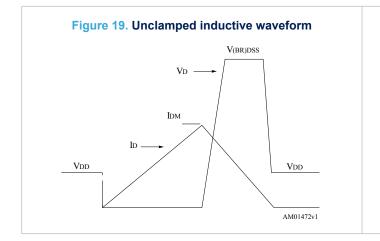


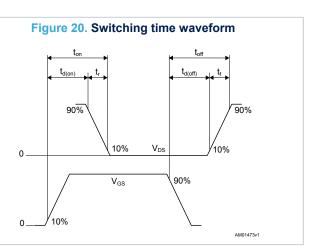
3 Test circuits













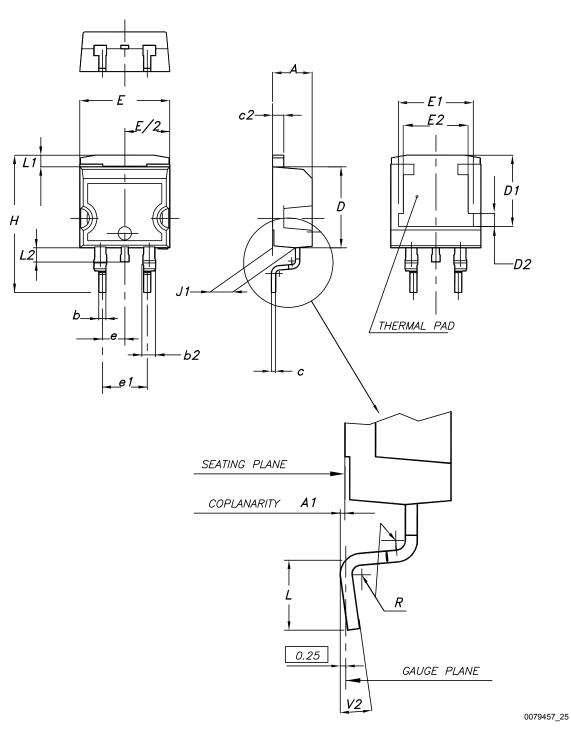
4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.



4.1 D²PAK (TO-263) type A package information

Figure 21. D²PAK (TO-263) type A package outline





Dim.		mm	
Dim.	Min.	Тур.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
С	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.30	8.50	8.70
E2	6.85	7.05	7.25
е		2.54	
e1	4.88		5.28
Н	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

Table 9. D²PAK (TO-263) type A package mechanical data



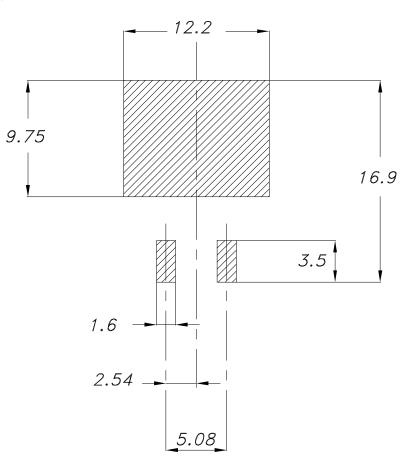
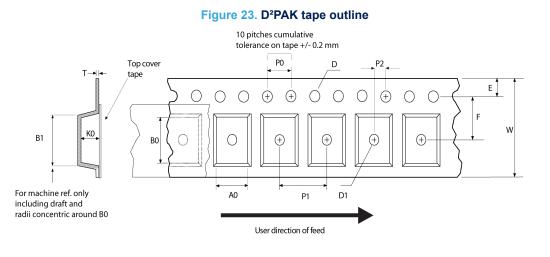


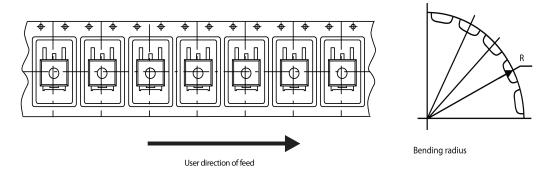
Figure 22. D²PAK (TO-263) recommended footprint (dimensions are in mm)

Footprint



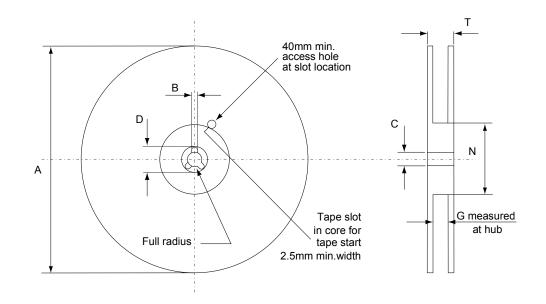
4.2 D²PAK packing information





AM08852v1

Figure 24. D²PAK reel outline



AM06038v1

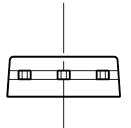
	Table 10. D ² PAK t	tape and reel	mechanical data
--	--------------------------------	---------------	-----------------

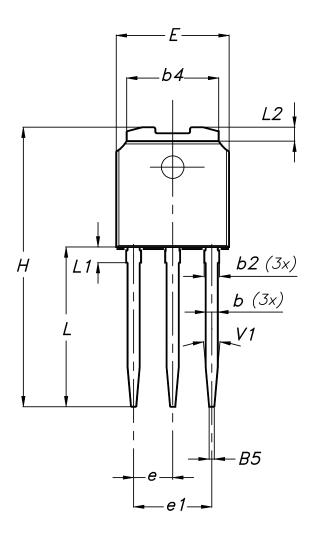
	Таре			Reel	
Dim.	mm		Dim.	m	m
Dim.	Min.	Max.	Dini.	Min.	Max.
A0	10.5	10.7	А		330
В0	15.7	15.9	В	1.5	
D	1.5	1.6	С	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
К0	4.8	5.0	Т		30.4
P0	3.9	4.1			1
P1	11.9	12.1	Base	quantity	1000
P2	1.9	2.1	Bulk	quantity	1000
R	50				
Т	0.25	0.35			
W	23.7	24.3			

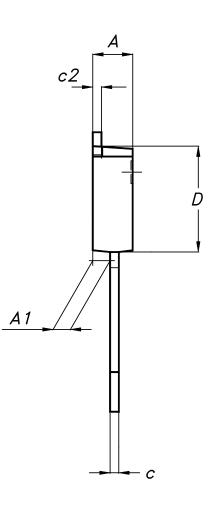


4.3 IPAK (TO-251) type A package information

Figure 25. IPAK (TO-251) type A package outline







0068771_IK_typeA_rev14



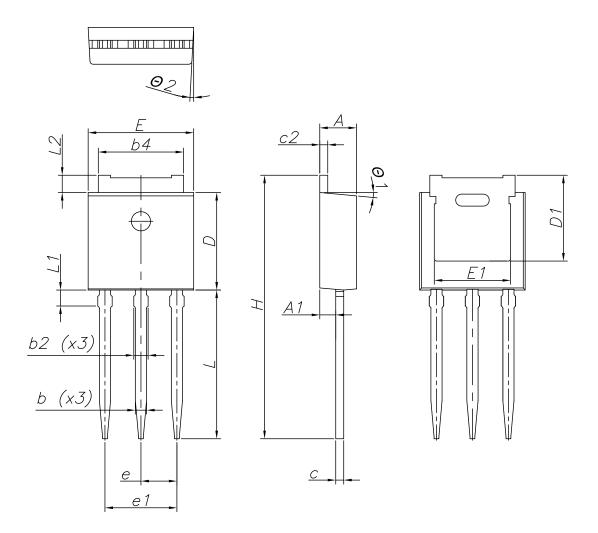
Dim.	mm			
D iin.	Min.	Тур.	Max.	
A	2.20		2.40	
A1	0.90		1.10	
b	0.64		0.90	
b2			0.95	
b4	5.20		5.40	
B5		0.30		
С	0.45		0.60	
c2	0.48		0.60	
D	6.00		6.20	
E	6.40		6.60	
e		2.28		
e1	4.40		4.60	
Н		16.10		
L	9.00		9.40	
L1	0.80		1.20	
L2		0.80	1.00	
V1		10°		

Table 11. IPAK (TO-251) type A package mechanical data



4.4 IPAK (TO-251) type C package information

Figure 26. IPAK (TO-251) type C package outline



0068771_IK_typeC_rev14



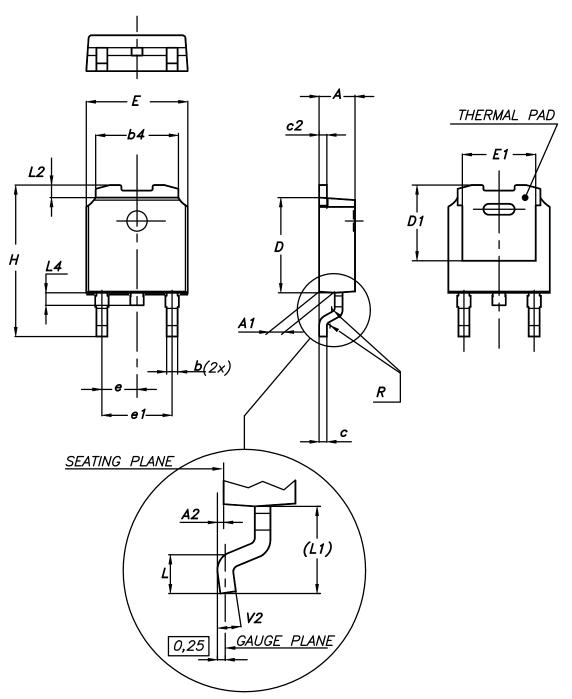
Dim.		mm	
Dini.	Min.	Тур.	Max.
A	2.20	2.30	2.35
A1	0.90	1.00	1.10
b	0.66		0.79
b2			0.90
b4	5.23	5.33	5.43
С	0.46		0.59
c2	0.46		0.59
D	6.00	6.10	6.20
D1	5.20	5.37	5.55
E	6.50	6.60	6.70
E1	4.60	4.78	4.95
е	2.20	2.25	2.30
e1	4.40	4.50	4.60
Н	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.80	1.00	1.20
L2	0.90	1.08	1.25
θ1	3°	5°	7°
θ2	1°	3°	5°

Table 12. IPAK (TO-251) type C package mechanical data



4.5 DPAK (TO-252) type A package information

Figure 27. DPAK (TO-252) type A package outline



0068772_A_25



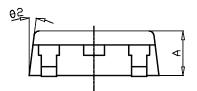
Dim.		mm	
Dim.	Min.	Тур.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
С	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
е	2.159	2.286	2.413
e1	4.445	4.572	4.699
Н	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

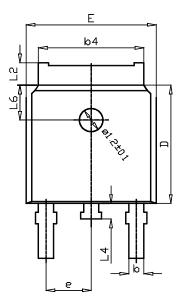
Table 13. DPAK (TO-252) type A mechanical data

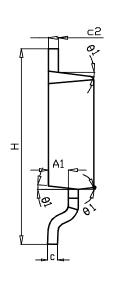


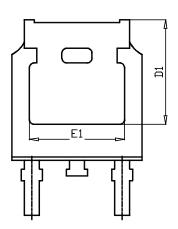
4.6 DPAK (TO-252) type C package information

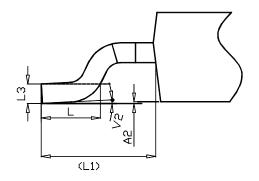
Figure 28. DPAK (TO-252) type C package outline











0068772_C_25



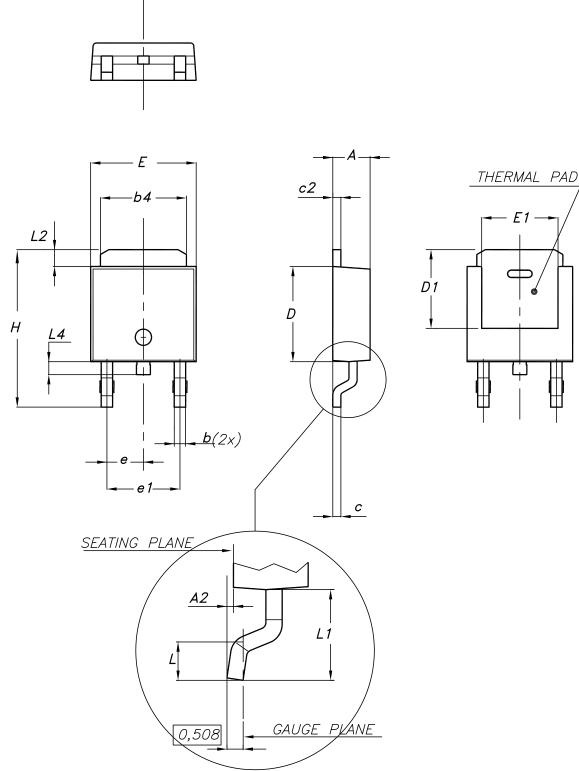
Dim.		mm	
Dim.	Min.	Тур.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
С	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.25		
E	6.50	6.60	6.70
E1	4.70		
e	2.186	2.286	2.386
Н	9.80	10.10	10.40
L	1.40	1.50	1.70
L1		2.90 REF	
L2	0.90		1.25
L3		0.51 BSC	·
L4	0.60	0.80	1.00
L6		1.80 BSC	
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

Table 14. DPAK (TO-252) type C mechanical data



4.7 DPAK (TO-252) type E package information

Figure 29. DPAK (TO-252) type E package outline



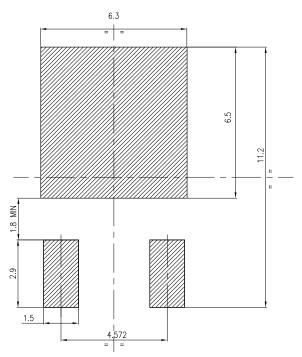
0068772_type-E_rev.25



Dim.	mm			
Dini.	Min.	Тур.	Max.	
A	2.18		2.39	
A2			0.13	
b	0.65		0.884	
b4	4.95		5.46	
С	0.46		0.61	
c2	0.46		0.60	
D	5.97		6.22	
D1	5.21			
E	6.35		6.73	
E1	4.32			
е		2.286		
e1		4.572		
Н	9.94		10.34	
L	1.50		1.78	
L1		2.74		
L2	0.89		1.27	
L4			1.02	

Table 15. DPAK (TO-252) type E mechanical data

Figure 30. DPAK (TO-252) recommended footprint (dimensions are in mm)

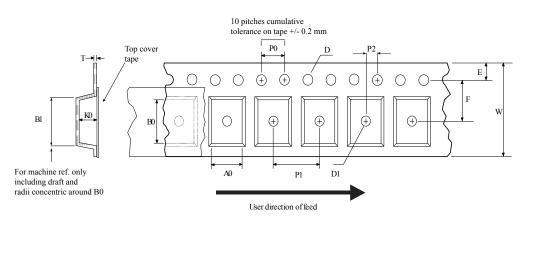


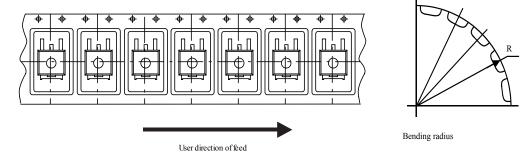
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4.8 DPAK (TO-252) packing information

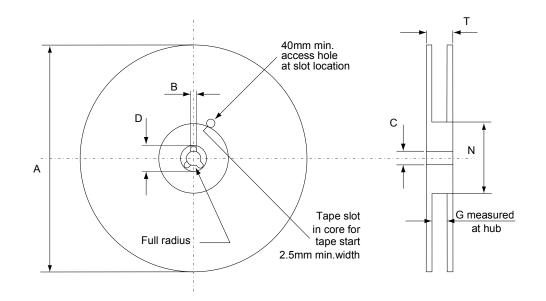
Figure 31. DPAK (TO-252) tape outline





AM08852v1





AM06038v1

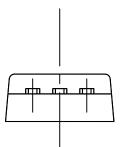
Table 16. DPAK (TO-252) tape and reel mechanical data

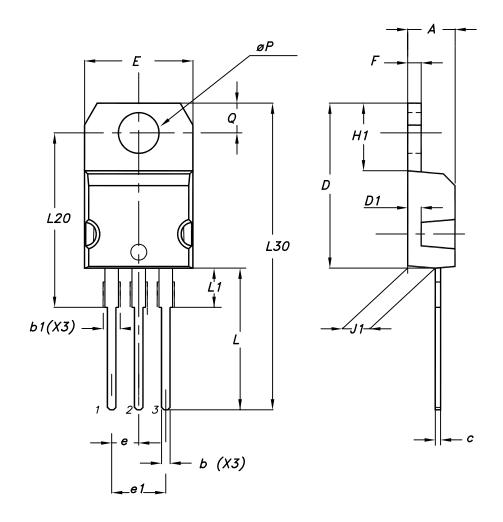
	Таре				
Dim.	mm		Dim	r	nm
Dim.	Min.	Max.	- Dim.	Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	В	1.5	
B1		12.1	С	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	Т		22.4
K0	2.55	2.75			
P0	3.9	4.1	Ba	se qty.	2500
P1	7.9	8.1	Bu	lk qty.	2500
P2	1.9	2.1			
R	40				
Т	0.25	0.35			
W	15.7	16.3			



4.9 TO-220 type A package information

Figure 33. TO-220 type A package outline





0015988_typeA_Rev_21



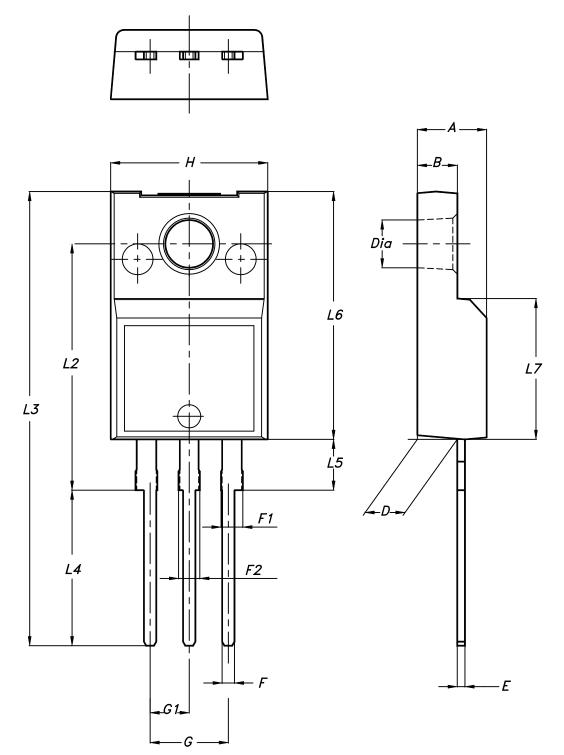
Dim.		mm	
Dini.	Min.	Тур.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
С	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
е	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

Table 17. TO-220 type A package mechanical data



4.10 TO-220FP package information

Figure 34. TO-220FP package outline



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Dim.	mm			
Dini.	Min.	Тур.	Max.	
A	4.4		4.6	
В	2.5		2.7	
D	2.5		2.75	
E	0.45		0.7	
F	0.75		1	
F1	1.15		1.70	
F2	1.15		1.70	
G	4.95		5.2	
G1	2.4		2.7	
Н	10		10.4	
L2		16		
L3	28.6		30.6	
L4	9.8		10.6	
L5	2.9		3.6	
L6	15.9		16.4	
L7	9		9.3	
Dia	3		3.2	

Table 18. TO-220FP package mechanical data



5 Ordering information

Order code	Marking	Package	Packing
STB3NK60ZT4	B3NK60Z	D ² PAK	Tape and reel
STD3NK60Z-1	D3NK60Z	IPAK	Tube
STD3NK60ZT4		DPAK	Tape and reel
STP3NK60Z	P3NK60Z	TO-220	Tube
STP3NK60ZFP	P3NK60ZFP	TO-220FP	Tube

Table 19. Order codes



Revision history

Table 20. Document revision history

Date	Version	Changes
07-Jul-2003	5	Updated document.
20-Aug-2018	6	Updated Section 1 Electrical ratings, Section 2 Electrical characteristics and Section 4 Package information. Minor text changes.



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	4.6	DPAK (TO-252) type C package information	0				
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